# Characterization of discharge based plasmas in the spectral range of 20-50 nm

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### CONTENT

- Motivation for 20 nm 50 nm
- Experimental set-up
- Results on emission for different gases
- Conclusions



#### Why dealing with 20-50 nm ?

- higher relative Mie scattering compared to 193 nm, benefit for defect inspection using 47 nm<sup>1</sup>
- increase of reflectivity with wavelength coming from lower wavelengths
- higher reflectance angle, better spatial resolution larger data set for reconstruction of parameters
  - characterization of layer systems
    spectroscopic reflectometry for periodic structure characterization<sup>2</sup>
- <sup>1</sup>Ref.: Barnes et al., SPIE Advanced Lithography 2017, Metrology, Inspection and Process control for Microlithography XXXI, Vol. 10145, 2017
- <sup>2</sup>Ref.: Bahrenberg et al., SPIE Advanced Lithography 2019, Metrology, Inspection and Process control for Microlithography XXXIII, Vol. 10959, 2019

#### Determination of Al<sub>2</sub>O<sub>3</sub> thickness on silicon substrate



Ref.: CXRO – The Center for X-Ray Optics (http://www.cxro.lbl.gov/)



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Determination of  $Al_2O_3$  thickness

on silicon substrate





#### **Opportunities and challenges with discharge plasmas**

- Starting point for development:
  - pinch plasma source optimized for 2-20 nm
  - electrical input energy ~ 2-10 J
  - average input power up to 10 kW
- Optimized emission for 20-50 nm is expected at lower plasma temperature/lower input energy
  - lower electrode erosion
  - longer maintenance interval
  - lower Cost of Ownership
- Planck radiator: lower temperature means broader wavelength interval
- Technical challenge to produce colder plasma with high density



Fraunhofer II T

**XUV** source





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#### **Experimental setup for 20 - 50 nm characterisation**

- Hollow Cathode Triggered pinch plasma:
  - repetition rate 20 Hz 30 Hz
  - input energy 1,3 J 2,3 J
  - operation with Ne, Ar, Kr, Xe
- emission spectra recorded with grazing incidence spectrograph (600 lines/mm)
- spectrally resolved end-on emission profile using slit perpendicular to entrance slit of spectrograph (Abel inversion)
- absolute emission estimated with photo diodes + spectral filters





#### Atomic data



Ref.: CHIANTI - An Atomic Database for Spectroscopic Diagnostics of Astrophysical Plasmas (https://chiantidatabase.org/sswidl/dbase/ar/)

Ref.: National Institute of Standards NIST – Atomic Spectra Database (https://nist.gov/pml/atomic-spectra-database)



Ne III

Ne IV

Ne V

Ne VI

Ne VII

**Ne VIII** 

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#### **Emission spectra (1)**





#### **Emission spectra (2)**





#### **Spatial profiles: Argon**





#### **Spatial profiles: Neon**





#### **Spatial profiles: Krypton, Xenon**

15

20

25

18.2 nm 20.1 nm 29.7 nm 37.4 nm 45.0 nm INTENSITY [ norm. ] 5000 4000 width [mm] 0,5 Krypton 3000 2000 -2 1000 0.0 -3 -2 -1 0 -4 15 40 45 50 20 25 30 35 RADIUS [ mm ] wavelength [ nm ] 22.5 nm 32.8 nm 41.5 nm 48.4 nm 16.5 nm 1,0 INTENSITY [ norm. ] 4000 3500 3000 width [mm] 2500 0,5 Xenon 2000 -2 1500

35

wavelength [ nm ]

30

40

45

1000 500

50



3

- 18.17 nm

20.10 nm 29.67 nm 37.36 nm

44.99 nm

1

0

RADIUS [ mm ]

1

-1

2

3

— 16.53 nm

22.53 nm 32.82 nm 41.48 nm

48.36 nm

2

4

1,0

0,0

-3

-2

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#### **Estimation of absolute emission**

- nine AXUV 100 diodes
- sensitivity from suppliers data sheet (~ 0,2 A/W )
- different coatings for discrimination of spectral ranges
- correction for self-absorption in beamline









#### **Overview emission spectra**



- emission spectra normalized to input energy (same scale for all elements !)
- expected total energy for Neon in wavelength interval 20-50 nm :  $E_{20-50} \sim 100 \text{ mJ}/2\pi \text{sr}$ (rough estimation !!) CE ~ 4 %/2 $\pi \text{sr}$

#### **Summary and conclusion**

- Investigation on 20 nm 50 nm emission of different gases in a ~2 J discharge plasma (Neon, Argon, Krypton, Xenon)
- Observed transitions of NeIV NeVI and ArVIII
- "Large" range of diameter for different gases and for different ionization levels (up to 4 mm for NeIV)
- **Highest conversion efficiency for Neon ~100 mJ/2\pisr (~4 %/2\pisr)**

see also poster S68: Vieker et al., The Effect of Gas Admixture on the Operation of a Discharge based EUV-Source



## THANK YOU !!

